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etching any unreacted silicon from said silicon cap layer.

4. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

*depositing a metal containing silicon or a metal alloy on a bulk silicon substrate;
reacting said metal containing silicon or said alloy to form a first silicide phase;
etching any unreacted metal containing silicon or alloy;
depositing a silicon cap layer over said first silicide phase;
reacting the silicon cap layer to form a second silicide phase; and
etching any unreacted silicon from said silicon cap layer.*

10. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

*depositing a metal or a metal alloy on a bulk silicon substrate;
reacting said metal or said alloy to form a first silicide phase;
etching any unreacted metal or alloy;
depositing a silicon cap layer over said first silicide phase;
reacting the silicon cap layer to form a second silicide phase; and
etching any unreacted silicon from said silicon cap layer,
wherein said metal is co-deposited with silicon.*

13. (Amended) A method for fabricating a silicide, said method comprising:

*providing a substrate having a silicon layer;
depositing a metal containing silicon or a metal alloy over said silicon layer;
reacting said metal containing silicon or said alloy to form a first silicide phase;*

etching any unreacted metal containing silicon or alloy; and
C4 Cont.
depositing a silicon cap layer over said metal containing silicon or said alloy;
reacting the silicon cap layer, to form a second silicide phase; and
etching any unreacted silicon from said silicon cap layer.

25. (Amended) A method for fabricating a silicide for a semiconductor device, said method comprising:

depositing a metal containing silicon or a metal alloy on a silicon substrate;
reacting said metal containing silicon or said alloy to form a first forming silicide phase;
etching any unreacted metal or alloy;
depositing a silicon cap layer over said first forming silicide phase;
reacting the silicon cap layer to form a second silicide phase, for said semiconductor
device; and
etching any unreacted silicon from said silicon cap layer.

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26. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

depositing a metal containing silicon or a metal alloy on a bulk silicon substrate;
reacting said metal containing silicon or said alloy to form a first silicide phase;
etching any unreacted metal containing silicon or alloy;
depositing a silicon cap layer over said first silicide phase;

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cont.

reacting the silicon cap layer to form a second phase; and
etching any unreacted silicon from said silicon cap layer, wherein said metal is nickel.

Please add the following new claims:

- D 27. The method of claim 1, wherein said first silicide phase comprises a silicon-rich phase.
28. The method of claim 1, wherein said depositing said metal containing silicon or said metal alloy is for extending a temperature window in which a silicide metal-rich phase exists.
- DH 29. The method of claim 4, wherein said first silicide phase comprises a silicon-rich phase.
- C 30. The method of claim 4, wherein said depositing said metal containing silicon or said metal alloy is for extending a temperature window in which a silicide metal-rich phase exists.
- D 31. The method of claim 10, wherein said first silicide phase comprises a silicon-rich phase.
32. The method of claim 10, wherein said depositing said metal containing silicon or said metal alloy is for extending a temperature window in which a silicide metal-rich phase exists.
- D 33. The method of claim 13, wherein said first silicide phase comprises a silicon-rich phase.